



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**REVOCATION OF PREVIOUS POWER  
OF ATTORNEY (37 C.F.R. § 1.36) AND  
NEW POWER OF ATTORNEY (37 C.F.R. § 1.32)**

Commissioner for Patents  
U.S. Patent & Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Siltronic AG is the Assignee of the entire right, title and interest of the U.S. patent applications as identified on the attached Exhibit A. Also attached is a Statement Under 37 C.F.R. § 3.73(b) Establishing Right of Assignee to Take Action in these applications.

The Assignee hereby revokes all previous Powers of Attorney given with respect to these applications in proceedings before the U.S. Patent and Trademark Office.

The Assignee further hereby appoints the practitioners associated with Customer Number 22045 to prosecute these applications to issue, to transact all business in the Patent Office connected therewith, and to receive the Letters Patents. Please address all correspondence to that Customer Number and direct all telephone calls to (248) 358-4400.

CUSTOMER NO.

**22045**

Revocation of Previous Power of Attorney  
(37 C.F.R. § 1.36) and New Power of Attorney (37 C.F.R. § 1.32)

The undersigned (whose title is supplied below) is authorized to act on behalf of the Assignee.

Siltronic AG, Assignee

Dated: April 20, 2005

Signature: 

Printed Name: Dr. Karl-Heinz Rimböck

Title: Vice President Corporate Intellectual Property

**CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8**

I hereby certify that this paper, including all enclosures referred to herein, is being deposited with the United States Postal Service as first-class mail, postage pre-paid, in an envelope addressed to: Commissioner for Patents, U.S. Patent & Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450 on:

April 26, 2005  
Date of Deposit

William G. Conger  
Name of Person Signing

  
Signature

## EXHIBIT A

<b>Inventor</b>	<b>Serial No.</b>	<b>Filing Date</b>	<b>Title</b>	<b>New Atty. Docket No.</b>
Tachikawa et al.	10/236,273	9/6/2002	Silicon Semiconductor Substrate and Preparation Thereof	<del>WSAG 0122 PUS</del>
Kishida et al.	10/283,683	10/30/2002	Single Crystal Production Method	WSAG 0123 PUS
Sasaki et al.	10/858,646	6/2/2004	SOI Substrate, Semiconductor Substrate, and Method for Production Thereof	WSAG 0124 PUS
Schnegg et al.	10/415,597	10/25/2001	Method for Assembling Planar Workpieces	WSAG 0127 PUSA
Virbulis et al.	10/053,446	1/17/2002	Process and Apparatus for Producing a Silicon Single Crystal	WSAG 0128 PUS
Murphy et al.	10/481,537	6/27/2002	Film or Layer made of Semi- Conductive Material and Method for Producing Said Film or Layer	WSAG 0129 PUSA
Pietsch et al.	10/209,121	7/31/2002	Semiconductor Wafer with Improved Local Flatness, and Method for its Production	WSAG 0130 PUS
Stadler et al.	10/686,365	10/15/2003	Process and Device for the Wet- Chemical Treatment of Silicon	WSAG 0131 PUS
Altmannshofer et al.	10/209,106	7/31/2002	Method and Device for the Production of a Single Crystal	WSAG 0132 PUS
Dantz et al.	10/351,739	1/27/2003	Silicon Single Crystal and Process for Producing It	WSAG 0133 PUS
VonAmmon et al.	10/350,570	1/24/2003	Process and Apparatus for Producing a Single Crystal of Semiconductor Material	WSAG 0134 PUS
Weber et al.	10/371,493	2/20/2003	Process for Producing a Highly Doped Silicon Single Crystal	WSAG 0135 PUS

<b>Inventor</b>	<b>Serial No.</b>	<b>Filing Date</b>	<b>Title</b>	<b>New Atty. Docket No.</b>
Becker et al.	10/410,841	4/10/2003	Filtering and Inerting of Combustible dusts in the Process Off-Gas	WSAG 0136 PUS
VonAmmon et al.	10/387,593	3/13/2003	Process and Apparatus for Epitaxially Coating a Semiconductor Wafer and Epitaxially Coated Semiconductor Wafer	WSAG 0137 PUS
VonAmmon et al.	11/020,947	12/23/2004	Process and Apparatus for Epitaxially Coating a Semiconductor Wafer and Epitaxially Coated Semiconductor Wafer	WSAG 0137 PUS1
Knobel et al.	10/410,812	4/10/2003	Doped Semiconductor Wafer of Float Zone Pulled Semiconductor Material, and Process for Producing the Semiconductor Wafer	WSAG 0138 PUS
Schwab et al.	10/877,682	6/25/2004	Process for the Wet-Chemical Surface Treatment of a Semiconductor Wafer	WSAG 0139 PUS
Weber et al.	10/690,415	10/21/2003	Process for Producing a Silicon Single Crystal Which is Doped with Highly Volatile Foreign Substances	WSAG 0140 PUS
Holzl et al.	10/853,322	5/25/2004	SOI Wafer and Process for Producing It	WSAG 0141 PUS
Weber et al.	10/732,119	12/10/2003	Silicon Single Crystal, and Process for Producing It	WSAG 0142 PUS
Teuschler et al.	10/762,111	1/21/2004	Polished Semiconductor Wafer and Process for Producing It	WSAG 0144 PUS
Seuring et al.	10/893,522	7/16/2004	Silicon Wafer and Process for Producing It	WSAG 0145 PUS

<b>Inventor</b>	<b>Serial No.</b>	<b>Filing Date</b>	<b>Title</b>	<b>New Atty. Docket No.</b>
Attenberger et al.	10/492,329	10/11/2002	Method for Forming a Layered Semiconductor Technology Structure and Corresponding Layered Semiconductor Technology Structure	WSAG 0146 PUSA
Hennhoefer et al.	09/032,305	2/27/1998	Process for Treating a Polished Semiconductor Wafer Immediately After the Semiconductor Wafer has been Polished	WSAG 0147 PUS
Brunner et al.	09/425,694	10/22/1999	Process for the Wet Chemical Treatment of Semiconductor Wafers	WSAG 0148 PUS
Wenski et al.	10/402,171	3/28/2003	Epitaxially Coated Semiconductor Wafer and Process for Producing It	WSAG 0149 PUS
Siebert et al.	10/731,034	12/9/2003	Epitaxially Coated Semiconductor Wafer and Process for Producing It	WSAG 0150 PUS

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**STATEMENT UNDER 37 C.F.R. § 3.73(b)  
ESTABLISHING RIGHT OF ASSIGNEE TO TAKE ACTION**


Commissioner for Patents  
U.S. Patent & Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Siltronic AG, a corporation of Germany, having its principal offices at Hanns-Seidel-Platz 4, 81737 Munich, Germany, is the assignee of the entire right, title and interest in the U.S. patent applications identified on the attached Exhibit A by virtue of an assignment from the inventor(s) thereof. The recordation date and reel/frame numbers of each said assignment is also reflected on the attached Exhibit A.

The undersigned (whose title is supplied below) is authorized to act on behalf of the Assignee.

Dated: April 26, 2005

Signature: 

Date: April 26, 2005

Printed Name: William G. Conger

Title: U.S. Patent Counsel for Siltronic AG

Brooks Kushman P.C.  
1000 Town Center Drive  
22nd Floor  
Southfield, Michigan 48075  
(248) 358-4400



### CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

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William G. Conger  
Name of Person Signing

Willi  
Signature

**EXHIBIT A**

<b>Serial No.</b>	<b>Filing Date</b>	<b>Reel/Frame</b>	<b>New Atty. Docket No.</b>
10/236,273	9/6/2002	013278/0340	WSAG 0122 PUS
10/283,683	10/30/2002	013424/0620	WSAG 0123 PUS
10/858,646	6/2/2004	015426/0668	WSAG 0124 PUS
10/415,597	08/22/2003	014413/0493	WSAG 0127 PUSA
10/053,446	3/15/2002	012724/0148	WSAG 0128 PUS
10/481,537	6/27/2002	015077/0943	WSAG 0129 PUSA
10/209,121	7/31/2002	013162/0272	WSAG 0130 PUS
10/686,365	3/15/2004	015072/0275	WSAG 0131 PUS
10/209,106	7/31/2002	013174/0988	WSAG 0132 PUS
10/351,739	1/27/2003	013708/0598	WSAG 0133 PUS
10/350,570	1/24/2003	013700/0477	WSAG 0134 PUS
10/371,493	11/13/2003	014124/0813	WSAG 0135 PUS
10/410,841	4/10/2003	013967/0682	WSAG 0136 PUS
10/387,593	6/12/2003	014158/0453	WSAG 0137 PUS
11/020,947	6/12/2003	014158/0453	WSAG 0137 PUS1
10/410,812	4/10/2003	013959/0019	WSAG 0138 PUS
10/877,682	6/25/2004	015771/0798	WSAG 0139 PUS
10/690,415	10/21/2003	014625/0365	WSAG 0140 PUS
10/853,322	5/25/2004	015396/0938	WSAG 0141 PUS
10/732,119	12/10/2003	014792/0614	WSAG 0142 PUS
10/762,111	2/9/2005	015741/0388	WSAG 0144 PUS
10/893,522	7/16/2004	015598/0353	WSAG 0145 PUS
10/492,329	5/19/2004	015337/0511	WSAG 0146 PUSA

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09/032,305	2/27/1998	9007/0473	WSAG 0147 PUS
09/425,694	10/27/1999	010343/0840	WSAG 0148 PUS
10/402,171	7/14/2000	011020/0737	WSAG 0149 PUS
10/731,034	11/20/2000	011303/0548	WSAG 0150 PUS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



**NOTICE TO CHANGE CORRESPONDENCE ADDRESS**

Commissioner for Patents  
U.S. Patent & Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Please change the correspondence address as identified on the attached Exhibit  
A to the following:

BROOKS KUSHMAN P.C.  
1000 Town Center  
22nd Floor  
Southfield, Michigan 48075

Respectfully submitted,

By

  
William G. Conger

Reg. No. 31,209

Attorney/Agent for Applicant

Date: April 26, 2005

BROOKS KUSHMAN P.C.  
1000 Town Center, 22nd Floor  
Southfield, MI 48075-1238  
Phone: 248-358-4400; Fax: 248-358-3351

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4/26/2005

Date of Deposit

William G. Conger

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Signature

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Haibara et al.	10/975,617	10/28/2004	Method for Forwarding Ozonated Water	WSAG 0125 PUS
Haibara et al.	10/975,510	10/28/2004	Method for Supply of Constant- Concentration Ozonated Water	WSAG 0126 PUS
Schnegg et al.	10/415,597	10/25/2001	Method for Assembling Planar Workpieces	WSAG 0127 PUSA
Virbulis et al.	10/053,446	1/17/2002	Process and Apparatus for Producing a Silicon Single Crystal	WSAG 0128 PUS
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VonAmmon et al.	10/350,570	1/24/2003	Process and Apparatus for Producing a Single Crystal of Semiconductor Material	WSAG 0134 PUS

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Holzl et al.	10/853,322	5/25/2004	SOI Wafer and Process for Producing It	WSAG 0141 PUS
Weber et al.	10/732,119	12/10/2003	Silicon Single Crystal, and Process for Producing It	WSAG 0142 PUS

New Atty.  
Docket No.

WSAG 0143 PUS

Inventor	Serial No.	Filing Date	Title	
VonAmmon et al.	10/809,070	03/24/2004	Method and Device for the Production of a Silicon Single Crystal, Silicone Single Crystal, and Silicon Semiconductor Wafers with Determined Defect Distributions	
Teuschler et al.	10/762,111	1/21/2004	Polished Semiconductor Wafer and Process for Producing It	WSAG 0144 PUS
Seuring et al.	10/893,522	7/16/2004	Silicon Wafer and Process for Producing It	WSAG 0145 PUS
Attenberger et al.	10/492,329	10/11/2002	Method for Forming a Layered Semiconductor Technology Structure and Corresponding Layered Semiconductor Technology Structure	WSAG 0146 PUSA
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Siebert et al.	10/731,034	12/9/2003	Epitaxially Coated Semiconductor Wafer and Process for Producing It	WSAG 0150 PUS